ON Semiconductor

Is Now



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Preferred Device

High Voltage Transistor

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	400	Vdc
Collector - Base Voltage	V _{CBO}	500	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	300	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

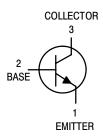
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{ heta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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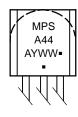
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MARKING DIAGRAM



TO-92 (TO-226AA) CASE 29-11 STYLE 1



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-	1		
Collector – Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)	V _(BR) CEO	400	_	Vdc
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, V_{BE} = 0$)	V _(BR) CES	500	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	V _{(BR)CBO}	500	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	6.0	-	Vdc
Collector Cutoff Current (V _{CB} = 400 Vdc, I _E = 0)	I _{CBO}	_	0.1	μAdc
Collector Cutoff Current (V _{CE} = 400 Vdc, V _{BE} = 0)	I _{CES}	_	500	nAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	_	0.1	μAdc
ON CHARACTERISTICS (Note 1)		•		•
DC Current Gain (Note 1) $ \begin{aligned} &(I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=50 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=100 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \end{aligned} $	h _{FE}	40 50 45 40	_ 200 _ _	-
Collector – Emitter Saturation Voltage (Note 1) ($I_C = 1.0 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$) ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}	- - -	0.4 0.5 0.75	Vdc
Base – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc)	V _{BE(sat)}	-	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS	-		•	
Output Capacitance (V _{CB} = 20 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	7.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	_	130	pF
Small–Signal Current Gain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 20 MHz)	h _{fe}	1.0	_	_

^{1.} Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSA44	TO-92	5000 Units / Box
MPSA44G	TO-92 (Pb-Free)	5000 Units / Box
MPSA44RL1	TO-92	2000 / Tape & Reel
MPSA44RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSA44RLRA	TO-92	2000 / Tape & Reel
MPSA44RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

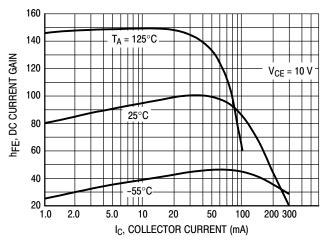


Figure 1. DC Current Gain

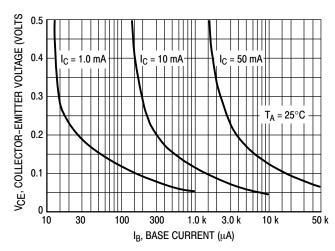


Figure 2. Collector Saturation Region

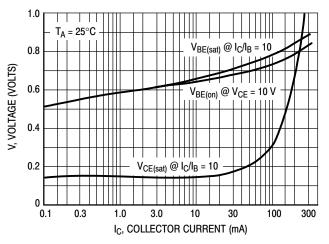


Figure 3. "On" Voltages

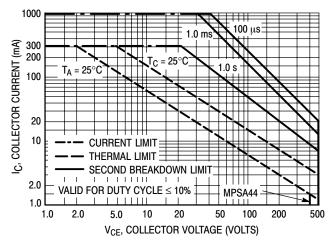


Figure 4. Active Region - Safe Operating Area

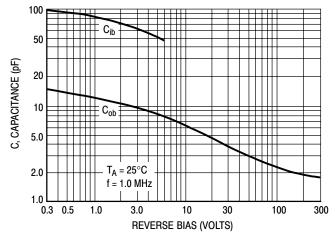


Figure 5. Capacitance

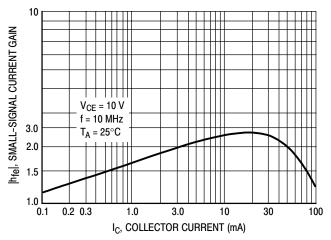


Figure 6. High Frequency Current Gain

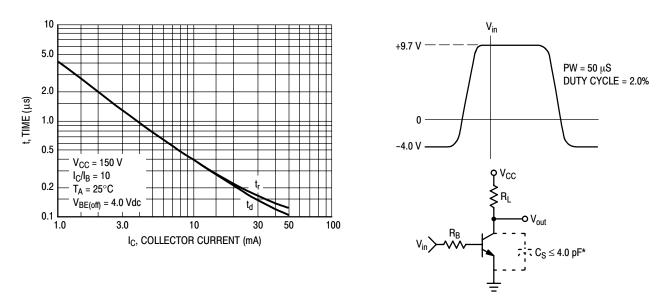


Figure 7. Turn-On Switching Times and Test Circuit

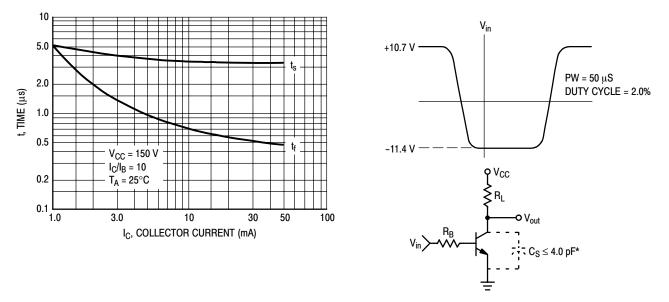
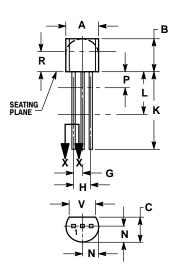


Figure 8. Turn-Off Switching Times and Test Circuit

*Total Shunt Capacitance or Test Jig and Connectors.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1: PIN 1.

EMITTER

BASE

3. COLLECTOR

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